

ABSTRACT OF THE DISCLOSURE

A method is disclosed for making a nano-size semiconductor component within a wide-bandgap semiconductor substrate. A first thermal energy beam is directed onto a first portion of the wide-bandgap semiconductor substrate to change the structure of the wide-bandgap semiconductor substrate into a first element of the semiconductor component. A second thermal energy beam is directed onto a second portion of the wide-bandgap semiconductor substrate adjacent to the first portion to form a second element of the semiconductor component.